

SAMTM data sheet SAM-800-1-5ps-x, λ = 800 nm

Laser wavelength $\lambda = 800 \text{ nm}$

High reflection band $\lambda = 780 ... 820 \text{ nm}$

Low intensity reflectivity $R_0 = 97.5 \%$ Scattering loss L = 1.5 %Absorbance $A_0 = 1 \%$ Modulation depth $\Delta R = 0.6 \%$

Saturation fluence $\Phi_{sat} = 100 \, \mu \text{J/cm}^2$

Relaxation time constant $\tau \sim 5 \text{ ps}$

Damage threshold $\Phi = 4 \text{ mJ/cm}^2$

Chip area 4.0 mm x 4.0 mm; other dimensions on request

Chip thickness 450 µm

Protection The SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

x = 0
x = 12.7 g
x = 25.4 g
x = 12.7 s
x = 25.4 s
x = 25.4 s
x = 25.0 w
x

Low intensity spectral reflectance and dispersion (GDD)

